

General Description

- Proprietary α MOS5™ technology
- Low $R_{DS(ON)}$
- Optimized switching parameters for better EMI performance
- Enhanced body diode for robustness and fast reverse recovery

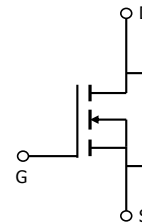
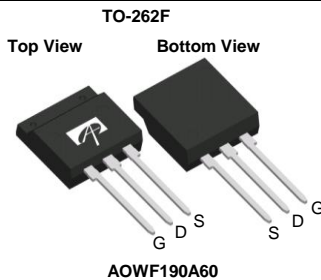
Applications

- SMPS with PFC, Flyback and LLC topologies
- Micro inverter with DC/AC inverter topology

Product Summary

$V_{DS} @ T_{j,max}$	700V
I_{DM}	80A
$R_{DS(ON),max}$	< 0.19 Ω
$Q_{g,typ}$	34nC
$E_{oss} @ 400V$	4.3 μ J

100% UIS Tested
 100% R_g Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOWF190A60	TO-262F	Tube	1000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	AOWF190A60	Units
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	20*
		$T_C=100^\circ\text{C}$	12*
Pulsed Drain Current ^C	I_{DM}	80	A
Avalanche Current ^C	I_{AR}	5	A
Repetitive avalanche energy ^C	E_{AR}	12.5	mJ
Single pulsed avalanche energy ^G	E_{AS}	410	mJ
MOSFET dv/dt ruggedness	dv/dt	100	V/ns
Peak diode recovery dv/dt		20	
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	27
		Derate above 25 $^\circ\text{C}$	0.22
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	T_L	300	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	AOWF190A60	Units
Maximum Junction-to-Ambient ^{A,D}	$R_{\theta JA}$	65	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Case	$R_{\theta JC}$	4.5	$^\circ\text{C}/\text{W}$

* Drain current limited by maximum junction temperature

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V, T _J =25°C	600	-	-	V
		I _D =250μA, V _{GS} =0V, T _J =150°C	-	700	-	
BV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D =250μA, V _{GS} =0V	-	0.59	-	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =600V, V _{GS} =0V	-	-	1	μA
		V _{DS} =480V, T _J =125°C	-	-	10	
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =5V, I _D =250μA	-	4	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =7.6A	-	0.17	0.19	Ω
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =10A	-	16	-	S
V _{SD}	Diode Forward Voltage	I _S =10A, V _{GS} =0V	-	0.85	1.2	V
I _S	Maximum Body-Diode Continuous Current		-	-	20	A
I _{SM}	Maximum Body-Diode Pulsed Current ^C		-	-	80	A
DYNAMIC PARAMETERS						
C _{ISS}	Input Capacitance	V _{GS} =0V, V _{DS} =100V, f=1MHz	-	1935	-	pF
C _{OSS}	Output Capacitance		-	55	-	pF
C _{O(er)}	Effective output capacitance, energy related ^H	V _{GS} =0V, V _{DS} =0 to 480V, f=1MHz	-	49	-	pF
C _{O(tr)}	Effective output capacitance, time related ^I		-	213	-	pF
C _{rSS}	Reverse Transfer Capacitance	V _{GS} =0V, V _{DS} =100V, f=1MHz	-	1.25	-	pF
R _g	Gate resistance	f=1MHz	-	5	-	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =480V, I _D =10A	-	34	-	nC
Q _{gs}	Gate Source Charge		-	12	-	nC
Q _{gd}	Gate Drain Charge		-	11	-	nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =400V, I _D =10A, R _G =25Ω	-	49	-	ns
t _r	Turn-On Rise Time		-	40	-	ns
t _{D(off)}	Turn-Off DelayTime		-	115	-	ns
t _f	Turn-Off Fall Time		-	26	-	ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =10A, di/dt=100A/μs, V _{DS} =400V	-	341	-	ns
I _{rm}	Peak Reverse Recovery Current		-	28	-	A
Q _{rr}	Body Diode Reverse Recovery Charge		-	6.8	-	μC

A. The value of R_{θJA} is measured with the device in a still air environment with T_A=25° C.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C, Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. L=60mH, I_{AS}=3.7A, V_{DD}=150V, R_G=25Ω, Starting T_J=25° C.

H. C_{O(er)} is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}.

I. C_{O(tr)} is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

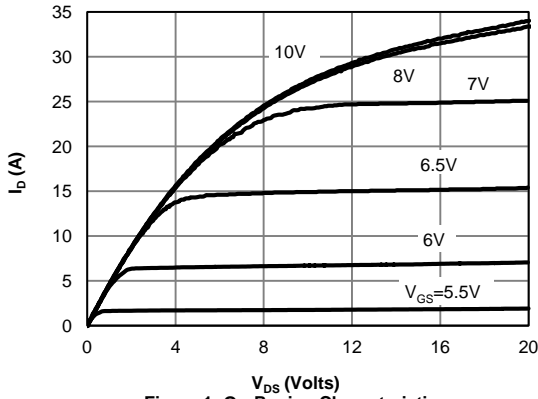


Figure 1: On-Region Characteristics

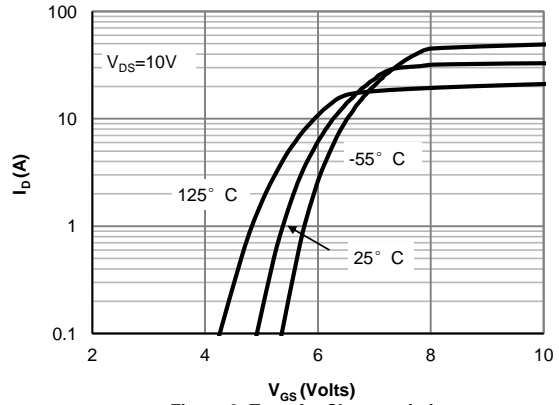


Figure 2: Transfer Characteristics

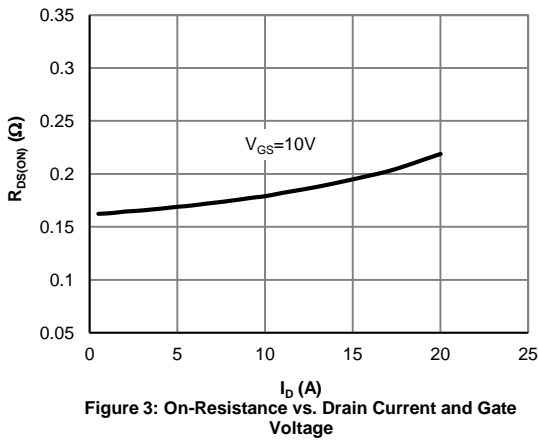


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

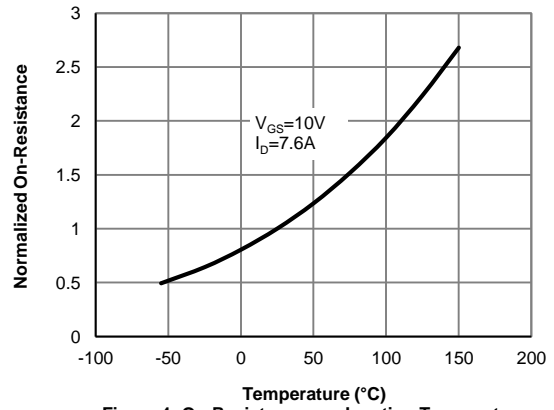


Figure 4: On-Resistance vs. Junction Temperature

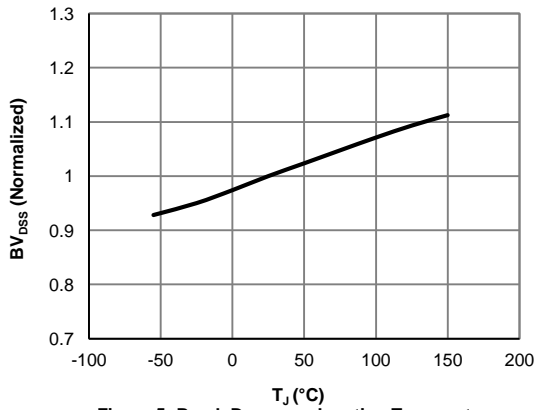


Figure 5: Break Down vs. Junction Temperature

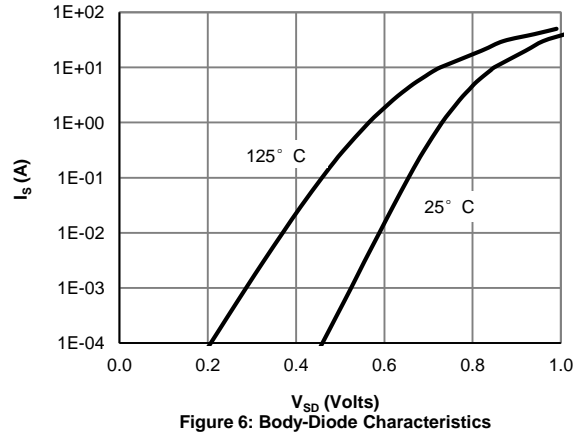


Figure 6: Body-Diode Characteristics

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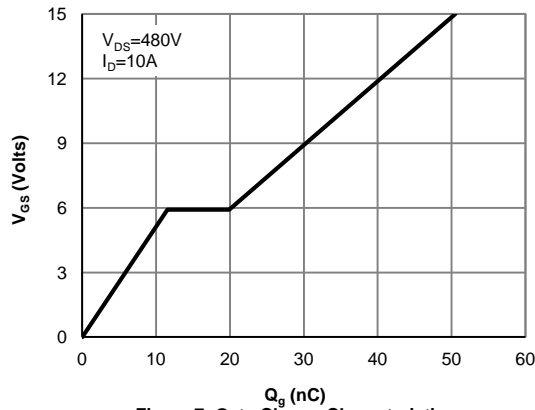


Figure 7: Gate-Charge Characteristics

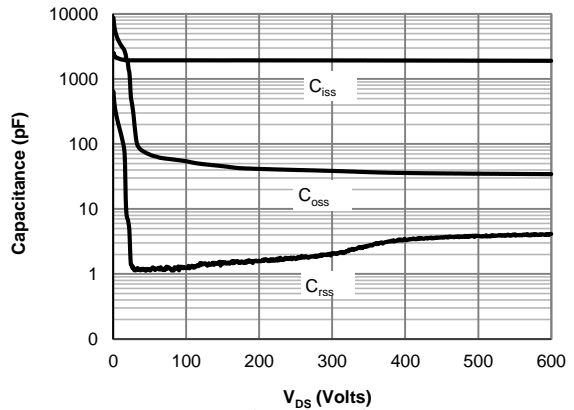


Figure 8: Capacitance Characteristics

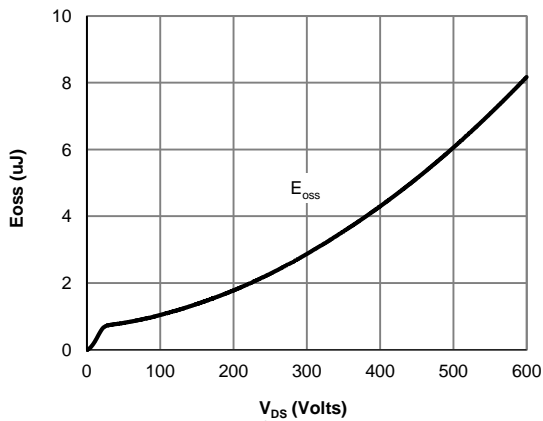


Figure 9: C_{oss} stored Energy

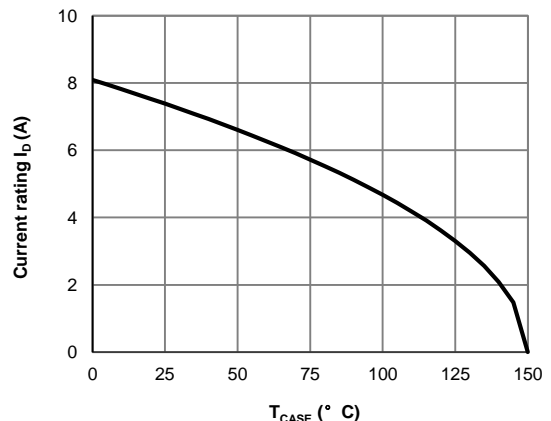


Figure 10: Current De-rating (Note F)

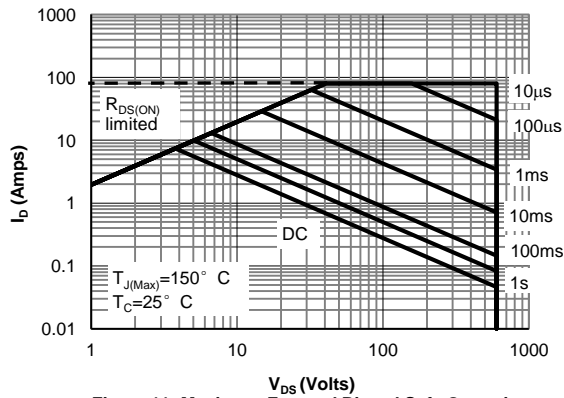


Figure 11: Maximum Forward Biased Safe Operating Area for AOWF190A60 (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

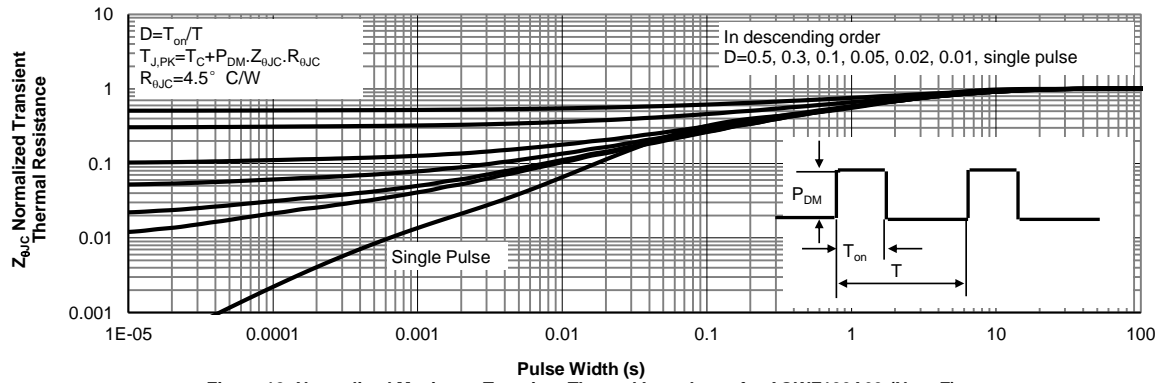
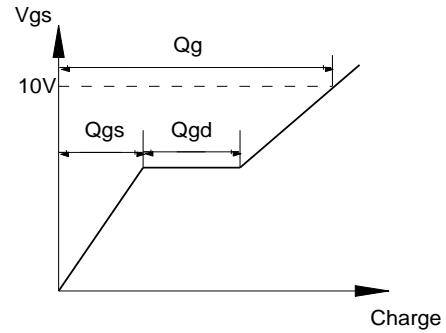
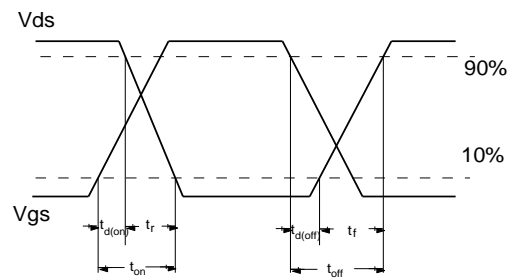
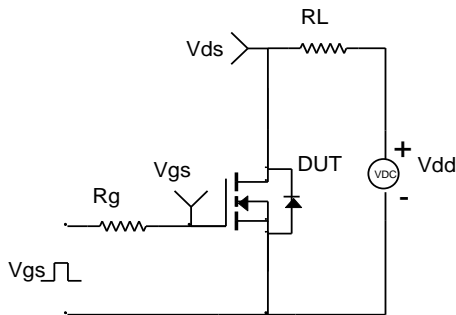


Figure 12: Normalized Maximum Transient Thermal Impedance for AOWF190A60 (Note F)

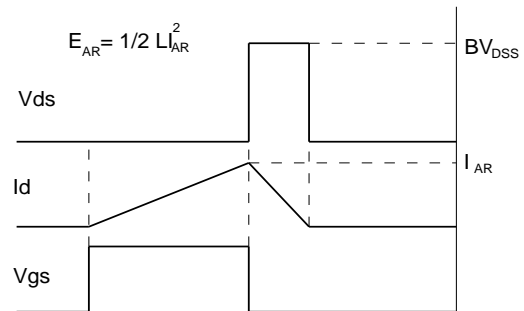
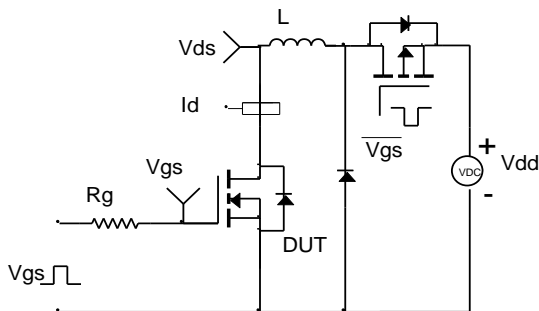
Gate Charge Test Circuit & Waveform



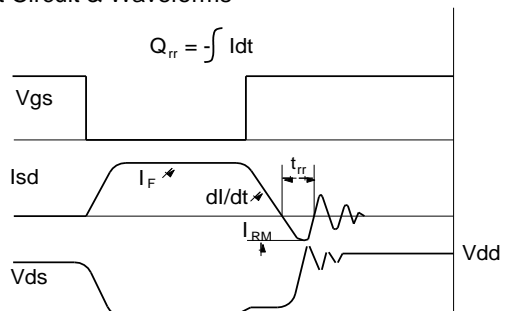
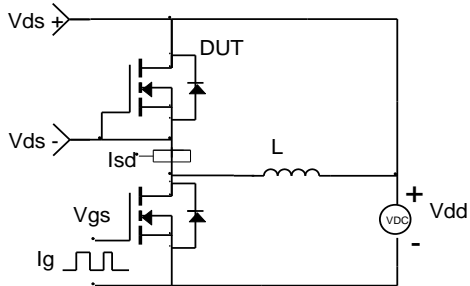
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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